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MMSS8550

Features

- SOT-23 Plastic-Encapsulate Transistors
- Capable of 0.625Watts(Tamb=25°C) of Power Dissipation.
- Collector-current 1.5A
- Collector-base Voltage 40V
- Operating and storage junction temperature range: -55°C to +150°C
- Marking Code: Y2

PNP Silicon Plastic-Encapsulate Transistor

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (I_C=100uAdc, I_E=0)	40	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (I_C=0.1mAdc, I_B=0)	25	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I_E=100uAdc, I_C=0)	6.0	---	Vdc
I_{CBO}	Collector Cutoff Current (V_{CB}=40Vdc, I_E=0)	---	0.1	uAdc
I_{CEO}	Collector Cutoff Current (V_{CE}=20Vdc, I_B=0)	---	0.1	uAdc
I_{EBO}	Emitter Cutoff Current (V_{EB}=5.0Vdc, I_C=0)	---	0.1	uAdc
ON CHARACTERISTICS				
$h_{FE(1)}$	DC Current Gain (I_C=100mAdc, V_{CE}=1.0Vdc)	120	350	---
$h_{FE(2)}$	DC Current Gain (I_C=800mAdc, V_{CE}=1.0Vdc)	40	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage (I_C=800mAdc, I_B=80mAdc)	---	0.5	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage (I_C=800mAdc, I_B=80mAdc)	---	1.2	Vdc
V_{EB}	Base- Emitter Voltage (I_E=1.5Adc)	---	1.6	Vdc
SMALL-SIGNAL CHARACTERISTICS				
f_T	Transistor Frequency (I_C=50mAdc, V_{CE}=10Vdc, f=30MHz)	100	---	MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	L	H
Range	120-200	200-350

SOT-23
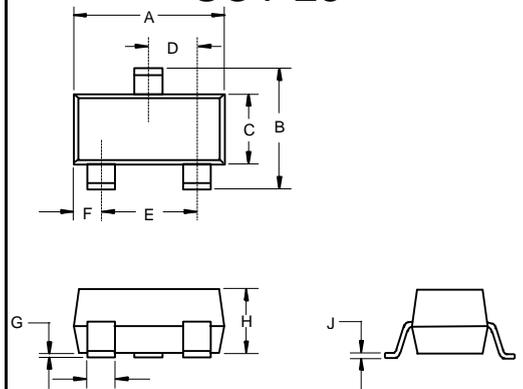
DIMENSIONS

DIM	INCHES MIN	INCHES MAX	MM MIN	MM MAX	NOTE
A	.110	.120	2.80	3.04	
B	.083	.098	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

Suggested Solder Pad Layout

inches
mm